SUPER HYPERABRupt TunING VARACTOR DIODES

FEATURES
- Mesa epitaxial silicon construction
- Silicon dioxide passivated
- Superior mid range linear characteristics
- High tuning ratios
- High Q
- Available in common cathode style
- Available in chip form (add suffix -000)

APPLICATIONS
- TCXOs, VCXOs
- Low voltage wireless open loop VCOs
- Low voltage wireless phase locked loop VCOs
- Phase shifters

SPECIFICATIONS
Reverse breakdown voltage at 10 μA DC (at 25°C): 12 V min
Maximum reverse leakage current at –10 V (at 25°C): 0.05 μA DC
Device dissipation at 25°C: 250 mW (derated linearly to zero at +125°C)
Operating junction temperature: –55°C to +125°C
Storage temperature: –55°C to +125°C

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<table>
<thead>
<tr>
<th>Total Capacitance C_T (pF) at –2 V</th>
<th>Total Capacitance C_T (pF) at –7 V</th>
<th>Total Capacitance C_T (pF) at –10 V</th>
<th>Q min at –2 V (10 MHz)</th>
<th>Model Number</th>
</tr>
</thead>
<tbody>
<tr>
<td>min</td>
<td>max</td>
<td>min</td>
<td>max</td>
<td>Single</td>
</tr>
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<tr>
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<td>150</td>
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<td>8.6</td>
<td>GVD1401-004</td>
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<tr>
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<td></td>
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</table>

SOT-23 PACKAGE - Consult factory for additional package configurations.
All dimensions are in /mm.
Unless otherwise specified, the tolerance on dimensions is ± 0.004 / 0.1.

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Super hyperabrupt tuning varactor diodes are designed for low voltage wireless applications, offering high Q and phase shift capabilities. They are available in both common cathode and chip form, providing flexibility in design. The reverse breakdown voltage, leakage current, and device dissipation values ensure reliable operation across a wide range of temperatures. These diodes are suitable for use in TCXOs, VCXOs, and other low voltage wireless systems.
SUPER HYPERABRUPT TUNING VARACTOR DIODES

FEATURES
- Mesa epitaxial silicon construction
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<table>
<thead>
<tr>
<th>Total Capacitance CT (pF) at –1 V</th>
<th>Capacitance Ratio C_T at –1 V / C_T at –3 V</th>
<th>Capacitance Ratio C_T at –1 V / C_T at –6 V</th>
<th>Q min at –4 V (50 MHz)</th>
<th>Model Number</th>
</tr>
</thead>
<tbody>
<tr>
<td>Total Capacitance CT (pF) at –1 V</td>
<td>min i max</td>
<td>min i max</td>
<td>min i max</td>
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</tr>
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<td>1.4</td>
<td>1.9</td>
<td>2.6</td>
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<td>5.85</td>
<td>7.15</td>
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<td>2.8</td>
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<td>10.35</td>
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<td>2.0</td>
<td>2.9</td>
</tr>
<tr>
<td>15.50</td>
<td>18.50</td>
<td>1.6</td>
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</tr>
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<td>1.6</td>
<td>2.0</td>
<td>3.5</td>
</tr>
</tbody>
</table>

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Unless otherwise specified, the tolerance on dimensions is ± 0.004 / 0.1.
SUPER HYPERABRupt Tuning Varactor Diodes

Features
- Mesa epitaxial silicon construction
- Silicon dioxide passivated
- Superior mid range linear characteristics
- High tuning ratios
- High Q
- Available in common cathode style
- Available in chip form (add suffix -000)

Applications
- TCXOs, VCXOs
- Low voltage wireless open loop VCOs
- Low voltage wireless phase locked loop VCOs
- Phase shifters

Specifications
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Maximum reverse leakage current at –10 V
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Device dissipation at 25°C: 250 mW (derated linearly to zero at +125°C)
Operating junction temperature: –55°C to +125°C
Storage temperature: –55°C to +125°C

Total Capacitance CT (pF) at –1 V
<table>
<thead>
<tr>
<th>Model Number</th>
<th>Single</th>
<th>Common Cathode</th>
</tr>
</thead>
<tbody>
<tr>
<td>GVD20442-001</td>
<td>13.0</td>
<td>6.5</td>
</tr>
<tr>
<td>GVD20443-001</td>
<td>13.0</td>
<td>6.5</td>
</tr>
<tr>
<td>GVD20444-001</td>
<td>17.0</td>
<td>8.5</td>
</tr>
<tr>
<td>GVD20445-001</td>
<td>17.0</td>
<td>8.5</td>
</tr>
<tr>
<td>GVD20446-001</td>
<td>26.0</td>
<td>13.0</td>
</tr>
<tr>
<td>GVD20447-001</td>
<td>26.0</td>
<td>13.0</td>
</tr>
<tr>
<td>GVD20448-001</td>
<td>36.0</td>
<td>18.0</td>
</tr>
<tr>
<td>GVD20449-001</td>
<td>36.0</td>
<td>18.0</td>
</tr>
</tbody>
</table>

Total Capacitance CT (pF) at –2.5 V
<table>
<thead>
<tr>
<th>Model Number</th>
<th>Single</th>
<th>Common Cathode</th>
</tr>
</thead>
<tbody>
<tr>
<td>GVD20442-004</td>
<td>10.0</td>
<td>2.7</td>
</tr>
<tr>
<td>GVD20443-004</td>
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</tr>
<tr>
<td>GVD20444-004</td>
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<td>3.2</td>
</tr>
<tr>
<td>GVD20445-004</td>
<td>13.0</td>
<td>3.2</td>
</tr>
<tr>
<td>GVD20446-001</td>
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<tr>
<td>GVD20447-001</td>
<td>20.0</td>
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<tr>
<td>GVD20448-001</td>
<td>27.0</td>
<td>6.2</td>
</tr>
<tr>
<td>GVD20449-001</td>
<td>27.0</td>
<td>6.2</td>
</tr>
</tbody>
</table>

Total Capacitance CT (pF) at –8 V
<table>
<thead>
<tr>
<th>Model Number</th>
<th>Single</th>
<th>Common Cathode</th>
</tr>
</thead>
<tbody>
<tr>
<td>GVD20444-001</td>
<td>2.7</td>
<td>750</td>
</tr>
<tr>
<td>GVD20444-001</td>
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<td>600</td>
</tr>
<tr>
<td>GVD20445-001</td>
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<td>300</td>
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<tr>
<td>GVD20446-001</td>
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<tr>
<td>GVD20449-001</td>
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<td>150</td>
</tr>
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</table>

Application:
- TCXOs, VCXOs
- Low voltage wireless open loop VCOs

SOT-23 Package - Consult factory for additional package configurations.
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SUPER HYPERABRupt TUNING VARACTOR DIODES

Surface Mount Low Parasitic Package (SMLP)

FEATURES
- Mesa epitaxial silicon construction
- Silicon dioxide passivated
- Fits footprint for SOD-323, SOD-123 and smaller
- High frequency (VHF to 8 GHz)
- Available on carrier and reel
- Available in chip form (add suffix -000)
- Two package styles including lower cost, flat top version
- Alternate notched termination version available, contact factory for outline drawing

APPLICATIONS
- PCS
- WANS
- DECT
- GSM
- TAGS
- AMPS
- Cellular

SPECIFICATIONS
Reverse breakdown voltage at 10 µA DC (at 25°C): 12 V min
Maximum reverse leakage current at –10 V (at 25°C): 0.05 µA DC
Device dissipation at 25°C: 250 mW (derated linearly to zero at +125°C)
Operating junction temperature: –65°C to +125°C
Storage temperature: –65°C to +125°C

<table>
<thead>
<tr>
<th>Total Capacitance C1 (pF) at –1 V min</th>
<th>Total Capacitance C1 (pF) at –2.5 V max</th>
<th>Total Capacitance C1 (pF) at –4 V min</th>
<th>Total Capacitance C1 (pF) at –8 V max</th>
<th>Q min at –4 V (50 MHz)</th>
<th>Model Number*</th>
</tr>
</thead>
<tbody>
<tr>
<td>36.0</td>
<td>18.0</td>
<td>27.0</td>
<td>12.0</td>
<td>6.2</td>
<td>400</td>
</tr>
<tr>
<td>26.0</td>
<td>13.0</td>
<td>20.0</td>
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<td>0.4</td>
<td>0.35</td>
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* For complete model number, select "Dash No." from chart below.

TERMINATIONS (GOLD PLATED)

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<th>Dash No.</th>
<th>A</th>
<th>B</th>
<th>C1</th>
<th>C2</th>
<th>D</th>
<th>K</th>
<th>L</th>
<th>M</th>
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</thead>
<tbody>
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<td>0.10</td>
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<td>0.035</td>
<td>0.050</td>
<td>0.015</td>
<td>0.004</td>
<td>0.030</td>
<td>0.070</td>
</tr>
<tr>
<td>- 111</td>
<td>2.5</td>
<td>1.3</td>
<td>0.89</td>
<td>1.3</td>
<td>0.38</td>
<td>0.1</td>
<td>0.76</td>
<td>1.8</td>
</tr>
<tr>
<td>- 012</td>
<td>0.12</td>
<td>0.060</td>
<td>0.035</td>
<td>0.050</td>
<td>0.020</td>
<td>0.005</td>
<td>0.030</td>
<td>0.080</td>
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<tr>
<td>- 112</td>
<td>3.0</td>
<td>1.5</td>
<td>0.89</td>
<td>1.3</td>
<td>0.51</td>
<td>0.1</td>
<td>0.76</td>
<td>2.0</td>
</tr>
<tr>
<td>- 013</td>
<td>0.200</td>
<td>0.100</td>
<td>0.035</td>
<td>0.050</td>
<td>0.020</td>
<td>0.005</td>
<td>0.030</td>
<td>0.120</td>
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<tr>
<td>- 113</td>
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<td>2.54</td>
<td>0.89</td>
<td>1.3</td>
<td>0.51</td>
<td>0.1</td>
<td>0.76</td>
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<td>0.035</td>
<td>0.050</td>
<td>0.015</td>
<td>0.004</td>
<td>0.030</td>
<td>0.070</td>
</tr>
<tr>
<td>- 114</td>
<td>1.9</td>
<td>1.3</td>
<td>0.89</td>
<td>1.3</td>
<td>0.38</td>
<td>0.1</td>
<td>0.76</td>
<td>1.8</td>
</tr>
<tr>
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<td>0.030</td>
<td>0.050</td>
<td>0.011</td>
<td>0.003</td>
<td>0.020</td>
<td>0.060</td>
</tr>
<tr>
<td>- 115</td>
<td>1.6</td>
<td>1.1</td>
<td>0.76</td>
<td>1.3</td>
<td>0.28</td>
<td>0.08</td>
<td>0.51</td>
<td>1.5</td>
</tr>
</tbody>
</table>

TERMINATIONS (SMD PLATED)

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Note: An SMLP package with three terminations sized to fit the pad layout for an SOT-23 package is also available. This package can be used for multiple diode designs (such as common cathode or common anode). Contact factory for the three-terminal SMLP outline drawing, and for further information on the multiple diode configurations.
WIDEBAND HYPERABRUPT TUNING VARACTOR DIODES

Microwave Hyperabrupt Series

FEATURES
- Mesa epitaxial silicon construction
- Silicon dioxide passivated
- Superior wide range linear characteristics
- High tuning ratios
- High Q
- Available in common cathode style
- Available in chip form (add suffix -000)

APPLICATIONS
- Low phase noise VCOs
- Phase locked loop VCOs
- High linearity VCOs
- Phase shifters

SPECIFICATIONS
Reverse breakdown voltage at 10 µA DC (at 25°C): 20 V min
Maximum reverse leakage current at -20 V (at 25°C): 0.05 µA DC
Device dissipation at 25°C: 250 mW (derated linearly to zero at +125°C)
Operating junction temperature: -55°C to +125°C
Storage temperature: -55°C to +125°C

<table>
<thead>
<tr>
<th>Total Capacitance C_T (pF) at -0 V</th>
<th>Total Capacitance C_T (pF) at -4 V</th>
<th>Total Capacitance C_T (pF) at -20 V</th>
<th>Q min at -4 V (50 MHz)</th>
<th>Model Number</th>
</tr>
</thead>
<tbody>
<tr>
<td>min</td>
<td>min</td>
<td>max</td>
<td></td>
<td>Single</td>
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<td>57</td>
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<td>2.50</td>
<td>0.52</td>
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<td>6.3</td>
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<td>0.96</td>
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<td>11.9</td>
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<td>0.94</td>
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<td>11.00</td>
<td>1.90</td>
<td>2.60</td>
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</tbody>
</table>

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WIDEBAND HYPERABRUPT TUNING VARACTOR DIODES
VHF/UHF Hyperabrupt Series

FEATURES
- Mesa epitaxial silicon construction
- Silicon dioxide passivated
- Superior wide range linear characteristics
- High tuning ratios
- High Q
- Available in common cathode style
- Available in chip form (add suffix -000)

APPLICATIONS
- Low phase noise VCOs
- Phase locked loop VCOs
- High linearity VCOs
- Phase shifters

SPECIFICATIONS
Reverse breakdown voltage at 10 µA DC
(at 25°C): 25 V min
Maximum reverse leakage current at -20 V
(at 25°C): 0.05 µA DC
Device dissipation at 25°C: 250 mW (derated linearly to zero at +125°C)
Operating junction temperature: -55°C to +125°C
Storage temperature: -55°C to +125°C

<table>
<thead>
<tr>
<th>Total Capacitance</th>
<th>Total Capacitance</th>
<th>Q min at -4 V</th>
<th>Model Number</th>
</tr>
</thead>
<tbody>
<tr>
<td>C&lt;sub&gt;T&lt;/sub&gt; (pF) at -3 V</td>
<td>C&lt;sub&gt;T&lt;/sub&gt; (pF) at -25 V</td>
<td>(50 MHz)</td>
<td>Single</td>
</tr>
<tr>
<td>min</td>
<td>max</td>
<td>min</td>
<td>max</td>
</tr>
<tr>
<td>9.5</td>
<td>14.5</td>
<td>1.8</td>
<td>2.8</td>
</tr>
<tr>
<td>9.5</td>
<td>14.5</td>
<td>1.8</td>
<td>2.8</td>
</tr>
<tr>
<td>26.0</td>
<td>32.0</td>
<td>4.3</td>
<td>6.0</td>
</tr>
<tr>
<td>26.0</td>
<td>32.0</td>
<td>4.3</td>
<td>6.0</td>
</tr>
</tbody>
</table>

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WIDEBAND HYPERABRUPT TUNING VARACTOR DIODES

VHF/UHF Hyperabrupt Series

FEATURES
- Mesa epitaxial silicon construction
- Silicon dioxide passivated
- Superior wide range linear characteristics
- High tuning ratios
- High Q
- Available in common cathode style
- Available in chip form (add suffix -000)

APPLICATIONS
- Low phase noise VCOs
- Phase locked loop VCOs
- High linearity VCOs
- Phase shifters

SPECIFICATIONS
Reverse breakdown voltage at 10 µA DC
(at 25°C): 22 V min
Maximum reverse leakage current at -20 V
(at 25°C): 0.05 µA DC
Device dissipation at 25°C: 250 mW (derated
linearly to zero at +125°C)
Operating junction temperature: -55°C to +125°C
Storage temperature: -55°C to +125°C

SOT-23 PACKAGE - Consult factory for additional package configurations.
All dimensions are in /mm.
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MICROWAVE HYPERABRUPT TUNING VARACTOR DIODES
Surface Mount Low Parasitic Package (SMLP)

FEATURES
- Mesa epitaxial silicon construction
- Silicon dioxide passivated
- Fits Footprint for SOD-323, SOD-123 and smaller
- High frequency (VHF to 8 GHz)
- Available on carrier and reel
- Available in chip form (add suffix -000)
- Two package styles including lower cost, flat top version
- Alternate notched termination version available, contact factory for outline drawing

APPLICATIONS
- PCS
- WANS
- AMPS
- GSM
- TAGS
- DECT
- Cellular

SPECIFICATIONS
Reverse breakdown voltage at 10 µA DC
(at 25°C): 22 V min
Maximum reverse leakage current at -20 V
(at 25°C): 0.05 µA DC
Device dissipation at 25°C: 250 mW (derated linearly to zero at +125°C)
Operating junction temperature: -65°C to +125°C
Storage temperature: -65°C to +125°C

<table>
<thead>
<tr>
<th>Total Capacitance C1 (pf) at 0 V</th>
<th>Total Capacitance C1 (pf) at -4 V</th>
<th>Total Capacitance C1 (pf) at -20 V</th>
<th>Q min at -4 V (50 MHz)</th>
<th>Model Number*</th>
</tr>
</thead>
<tbody>
<tr>
<td>Typical</td>
<td>min</td>
<td>max</td>
<td>max</td>
<td></td>
</tr>
<tr>
<td>26.0</td>
<td>8.75</td>
<td>10.80</td>
<td>1.85</td>
<td>2.50</td>
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<td>14.0</td>
<td>4.45</td>
<td>5.50</td>
<td>0.85</td>
<td>1.30</td>
</tr>
<tr>
<td>7.0</td>
<td>2.65</td>
<td>3.30</td>
<td>0.65</td>
<td>0.90</td>
</tr>
<tr>
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<td>1.75</td>
<td>2.20</td>
<td>0.50</td>
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</tr>
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<td>3.0</td>
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<td>0.40</td>
<td>0.55</td>
</tr>
<tr>
<td>2.0</td>
<td>0.85</td>
<td>1.10</td>
<td>0.30</td>
<td>0.45</td>
</tr>
</tbody>
</table>

* For complete model number, select “Dash No.” from chart below.

TERMINATIONS (GOLD PLATED)

All dimensions are in /mm.
Unless otherwise specified, the tolerance on dimensions is ± 0.003/0.08.

Note: An SMLP package with three terminations sized to fit the pad layout for an SOT-23 package is also available. This package can be used for multiple diode designs (such as common cathode or common anode). Contact factory for the three-terminal SMLP outline drawing, and for further information on the multiple diode configurations.
HIGH Q ABRUPT TUNING VARACTOR DIODES

FEATURES
- Mesa epitaxial silicon construction
- Silicon dioxide passivated
- Economy price
- Mil grade performance
- High Q
- Available in common cathode style
- Available in chip form (add suffix -000)

APPLICATIONS
- Low phase noise VCOs
- Phase locked loop VCOs
- Moderate bandwidth VCOs

SPECIFICATIONS
Reverse breakdown voltage at 10 µA DC
(at 25°C): 30 V min
Maximum reverse leakage current at -25 V
(at 25°C): 0.05 µA DC
Device dissipation at 25°C: 250 mW (derated linearly to zero at +125°C)
Operating junction temperature: -55°C to +125°C
Storage temperature: -55°C to +125°C

<table>
<thead>
<tr>
<th>Total Capacitance Ct (pF) at -4 V (±10%)</th>
<th>Capacitance Ratio</th>
<th>Q min at -4 V (50 MHz)</th>
<th>Model Number</th>
</tr>
</thead>
<tbody>
<tr>
<td></td>
<td>Ct at 0 V</td>
<td>Ct at -30 V min</td>
<td>Single</td>
</tr>
<tr>
<td>1.2</td>
<td>3.4</td>
<td></td>
<td>GVD1202-001</td>
</tr>
<tr>
<td>1.5</td>
<td>3.5</td>
<td></td>
<td>GVD1203-001</td>
</tr>
<tr>
<td>1.8</td>
<td>3.5</td>
<td></td>
<td>GVD1204-001</td>
</tr>
<tr>
<td>2.2</td>
<td>3.7</td>
<td></td>
<td>GVD1205-001</td>
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<td></td>
<td>GVD1206-001</td>
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<td>3.3</td>
<td>3.8</td>
<td></td>
<td>GVD1207-001</td>
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<td>3.9</td>
<td></td>
<td>GVD1208-001</td>
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<tr>
<td>4.7</td>
<td>3.9</td>
<td></td>
<td>GVD1209-001</td>
</tr>
<tr>
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<td>4.0</td>
<td></td>
<td>GVD1210-001</td>
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<td>4.0</td>
<td></td>
<td>GVD1211-001</td>
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<td>4.0</td>
<td></td>
<td>GVD1212-001</td>
</tr>
<tr>
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<td>4.1</td>
<td></td>
<td>GVD1213-001</td>
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</tr>
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<td></td>
<td>GVD1216-001</td>
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<tr>
<td>22.0</td>
<td>4.2</td>
<td></td>
<td>GVD1217-001</td>
</tr>
</tbody>
</table>

SOT-23 PACKAGE - Consult factory for additional package configurations.
All dimensions are in /mm.
Unless otherwise specified, the tolerance on dimensions is ± 0.004 / 0.1.
VARACTOR DIODES

MICROWAVE ABRUPT TUNING VARACTOR DIODES

Surface Mount Low Parasitic Package (SMLP)

FEATURES
- Mesa epitaxial silicon construction
- Silicon dioxide passivated
- Fits Footprint for SOD-323, SOD-123 and smaller
- High Frequency (VHF to 8 GHz)
- Available on carrier and reel
- Available in chip form (add suffix -000)
- Two package styles including lower cost, flat top version
- Alternate notched termination version available, contact factory for outline drawing

APPLICATIONS
- PCS
- WANS
- AMPS
- GSM
- TAGS
- DECT
- Cellular

SPECIFICATIONS
Reverse breakdown voltage at 10 µA DC (at 25°C): 30 V min
Maximum reverse leakage current at -25 V (at 25°C): 0.05 µA DC
Device dissipation at 25°C: 250 mW (derated linearly to zero at +125°C)
Operating junction temperature: -65°C to +125°C
Storage temperature: -65°C to +125°C

<table>
<thead>
<tr>
<th>Capacitance Ratio</th>
<th>Capacitance Ratio</th>
<th>Q min (50 MHz)</th>
<th>Model Number*</th>
</tr>
</thead>
<tbody>
<tr>
<td>C1 (pF) at -4 V</td>
<td>C1 at 0 V</td>
<td>C1 at -4 V</td>
<td>C1 at -30 V</td>
</tr>
<tr>
<td>0.8</td>
<td>1.5</td>
<td>1.45</td>
<td>3900</td>
</tr>
<tr>
<td>1.0</td>
<td>1.6</td>
<td>1.55</td>
<td>3800</td>
</tr>
<tr>
<td>1.2</td>
<td>1.7</td>
<td>1.60</td>
<td>3700</td>
</tr>
<tr>
<td>1.5</td>
<td>1.8</td>
<td>1.65</td>
<td>3600</td>
</tr>
<tr>
<td>1.8</td>
<td>1.9</td>
<td>1.70</td>
<td>3500</td>
</tr>
<tr>
<td>2.2</td>
<td>2.0</td>
<td>1.75</td>
<td>3400</td>
</tr>
<tr>
<td>2.7</td>
<td>2.0</td>
<td>1.80</td>
<td>3300</td>
</tr>
<tr>
<td>3.3</td>
<td>2.1</td>
<td>1.85</td>
<td>3100</td>
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<tr>
<td>3.9</td>
<td>2.1</td>
<td>1.90</td>
<td>2700</td>
</tr>
<tr>
<td>4.7</td>
<td>2.2</td>
<td>1.95</td>
<td>2600</td>
</tr>
<tr>
<td>5.6</td>
<td>2.2</td>
<td>2.00</td>
<td>2500</td>
</tr>
</tbody>
</table>

*For complete model number, select “Dash No.” from chart below.

TERMINATIONS (GOLD PLATED)

DASH INDICATES CATHODE END

BOTTOM VIEW

TOP VIEW

EPOXY ENCAPSULANT

SIDE VIEW FOR -01__

SIDE VIEW FOR -11__

MOUNTING PAD LAYOUT

All dimensions are in /mm. Unless otherwise specified, the tolerance on dimensions is ± 0.003/0.08.
Note: An SMLP package with three terminations sized to fit the pad layout for an SOT-23 package is also available. This package can be used for multiple diode designs (such as common cathode or common anode). Contact factory for the three-terminal SMLP outline drawing, and for further information on the multiple diode configurations.
MINIATURE MICROWAVE SILICON VARACTOR DIODES
Surface Mount Monolithic Package (SMMP)

FEATURES
- Multilayer construction
- Low SMT profile
- Low series inductance
- Low parasitic capacitance (0.06 pF)
- High Q
- Available on carrier and reel

APPLICATIONS
Microwave Voltage Controlled Oscillators (VCOs)
Ideal for Wide Bandwidth Applications (VHF-10 GHz)

SPECIFICATIONS
Reverse breakdown voltage at 10 µA DC
(at 25°C): See below
Maximum reverse leakage current at -10 V
(at 25°C): 0.05 µA DC
Operating junction temperature: -65°C to +125°C
Storage temperature: -65°C to +125°C

<table>
<thead>
<tr>
<th>Total Capacitance Ratio</th>
<th>Capacitance Ratio</th>
<th>Capacitance Ratio</th>
<th>Q min (50 MHz)</th>
<th>Model Number</th>
</tr>
</thead>
<tbody>
<tr>
<td>C&lt;sub&gt;T&lt;/sub&gt; (pF) at -1 V</td>
<td>C&lt;sub&gt;T&lt;/sub&gt; at -1 V</td>
<td>C&lt;sub&gt;T&lt;/sub&gt; at -6 V</td>
<td>max</td>
<td>min</td>
</tr>
<tr>
<td>2.6</td>
<td>1.4</td>
<td>2.6</td>
<td>3.6</td>
<td>1500</td>
</tr>
</tbody>
</table>

Reverse breakdown voltage at 10 µA DC: 15 V min

<table>
<thead>
<tr>
<th>Total Capacitance Ratio</th>
<th>Capacitance Ratio</th>
<th>Capacitance Ratio</th>
<th>Q min (50 MHz)</th>
<th>Model Number</th>
</tr>
</thead>
<tbody>
<tr>
<td>C&lt;sub&gt;T&lt;/sub&gt; (pF) at -1 V</td>
<td>C&lt;sub&gt;T&lt;/sub&gt; at -4 V</td>
<td>C&lt;sub&gt;T&lt;/sub&gt; at -20 V</td>
<td>max</td>
<td>min</td>
</tr>
<tr>
<td>3.25</td>
<td>0.2</td>
<td>0.45</td>
<td>1000</td>
<td></td>
</tr>
</tbody>
</table>

Reverse breakdown voltage at 10 µA DC: 22 V min

Models shown above supplied bulk in vials.
For 300 pc gel pack, add "-03" to the model number.
For 5000 pc carrier and reel, add "-50" to the model number.

All dimensions are in /mm.
Unless otherwise specified, the tolerance on dimensions is ± 0.004/0.1.